

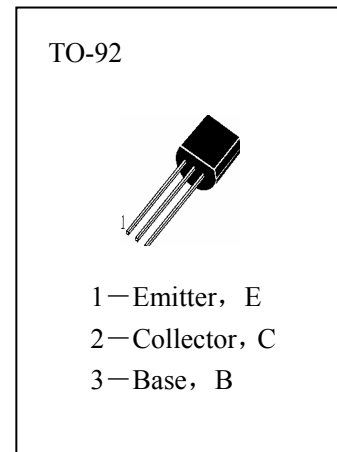


APPLICATIONS

High Voltage switching Applications.

ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

T _{stg}	Storage Temperature	-55~150°C
T _j	Junction Temperature	150°C
P _C	Collector Dissipation	700mW
V _{CBO}	Collector-Base Voltage	180V
V _{CEO}	Collector-Emitter Voltage	160V
V _{EBO}	Emitter-Base Voltage	6V
I _C	Collector Current	0.7A
I _{CP}	Collector Current (Pulse)	1.5A



ELECTRICAL CHARACTERISTICS (T_a=25°C)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV _{CBO}	Collector-Base Breakdown Voltage	180			V	I _C =10 μ A, I _E =0
BV _{CEO}	Collector-Emitter Breakdown Voltage	160			V	I _C =1mA, I _B =0
BV _{EBO}	Emitter-Base Breakdown Voltage	6			V	I _E =10 μ A, I _C =0
I _{CBO}	Collector Cut-off Current			0.1	μ A	V _{CB} =120V, I _E =0
I _{EBO}	Emitter Cut-off Current			0.1	μ A	V _{EB} =4V, I _C =0
H _{FE} (1)	DC Current Gain	100		400		V _{CE} =5V, I _C =100mA
H _{FE} (2)	DC Current Gain	80				V _{CE} =5V, I _C =10mA
V _{CE(sat)}	Collector- Emitter Saturation Voltage		0.12	0.4	V	I _C =250mA, I _B =25mA
V _{BE(sat)}	Base-Emitter Saturation Voltage		0.85	1.2	V	I _C =250mA, I _B =25mA
f _T	Current Gain-Bandwidth Product		120		MHz	V _{CE} =10V, I _C =50mA
C _{ob}	Output Capacitance		8		pF	V _{CB} =10V, I _E =0
t _{ON}	Turn-on Time		50		nS	
t _{STG}	Storage Time		1000		nS	See specified test circuit
t _F	Fall Time		60		nS	

h_{FE} Classification

R	S	T
100—200	140—280	200—400

switching test Circuit:

